

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	13	US-6217969-\$. DID. OR JP- 05339057-\$.DID. OR JP-02111663-\$. DID. OR JP- 6080295-\$.DID. OR JP-04128369-\$. DID. OR JP- 08183661-\$.DID. OR JP-05070230-\$. DID. OR JP- 11061394-\$.DID.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/02 10:41
S2	2	JP-2000104161-\$. DID.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/02 10:42
S3	9	((SHO) near2 (KUMAGAI)).INV.	US-PGPUB; USPAT	ADJ	ON	2008/06/02 10:42
S4	20	((FUMIO) near2 (ODAKA)).INV.	US-PGPUB; USPAT	ADJ	ON	2008/06/02 10:42
S5	42	((SHIGEKI) near2 (ENDO)).INV.	US-PGPUB; USPAT	ADJ	ON	2008/06/02 10:42
S6	340	refract\$4 near3 index with ("4.16" or "4.10" or "4.00" or "3.9" or S3 or S2 or S1)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/02 11:14
S7	2	refract\$4 near3 index with ("4.16" or "4.10" or "4.00" or "3.9" or S3 or S2 or S1) with (SiC or silicon carbide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/02 11:15
S8	21	refract\$4 near3 index with ("4.16" or "4.10" or "4.00" or "3.9" or S3 or S2 or S1) with (SiC or silicon carbide or silicon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/02 11:16

S9	654	refract\$4 near3 index with (SiC or silicon carbide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/02 11:18
S10	7	refract\$4 near3 index with (SiC or silicon carbide) same "633"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/02 11:19
S11	21	silicon carbide with target same volume	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/02 15:32
S12	8159	silicon carbide with silicon same volume	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/02 15:35
S13	124	silicon carbide with silicon same volume and "204"/ \$.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/02 15:35
S14	8	silicon carbide with silicon same target same volume and "204"/ \$.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/02 15:35
S15	287	silicon carbide same (particles or powder) same target	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/02 15:43
S16	23	silicon carbide same (particles or powder) same (micron or micrometer) same target	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/02 15:45

S17	5	silicon carbide with volume with target and "204"/\$. ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/02 18:10
S18	13	silicon carbide with volume with target and sputter \$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 07:31
S19	240	silicon carbide with volume near3 ratio	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 07:59
S20	45	silicon carbide with volume near3 ratio with ("50" or "55" or "60" or "65" or "70")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 08:00
S21	45	silicon carbide with silicon with volume near3 ratio with ("50" or "55" or "60" or "65" or "70")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 08:21
S22	57	(SiC or silicon carbide) with (silicon or Si) with volume near3 ratio with ("50" or "55" or "60" or "65" or "70")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 08:21
S23	1	08-183661	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 09:06
S24	2	"08183661"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 09:06

S25	3	"05270917"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 09:08
S26	29	silicon carbide with impregnat\$3 and "204"/\$.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 09:13
S27	25	silicon carbide with solvent with calcine\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 09:31
S28	1	(09/941676).APP.	USPAT; USOCR	ADJ	ON	2008/06/03 09:32
S29	0	silicon carbide with solvent with calcine\$3 and target and sputter \$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 09:53
S30	1	silicon carbide with solvent same calcine\$3 and target and sputter \$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 09:53
S31	1	silicon carbide same solvent same calcine\$3 and target and sputter\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 09:53
S32	10	US-5589116-\$. DID. OR US- 5002000-\$.DID. OR US-6228283-\$. DID. OR US- 4284431-\$.DID. OR US-6217969-\$. DID.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/03 10:13

S33	143	silicon carbide near3 target and sputter\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 10:14
S34	37	silicon carbide near3 target and sputter\$3 and "204"/\$.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 10:15
S35	0	silicon carbide near3 slurry with dry\$3 and sputter \$3 and "204"/\$. ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 10:37
S36	1	silicon carbide with slurry with dry \$3 and sputter\$3 and "204"/\$.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 10:37
S37	2	silicon carbide with slurry with dry \$3 and "204"/\$. ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 10:41
S38	2	silicon carbide with slurry same dry\$3 and "204"/\$. ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 10:42
S39	26	silicon carbide slurry same dry\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 10:43
S40	343	silicon carbide with slurry same dry\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 10:43

S41	0	refract\$4 near3 index with (SiC or silicon carbide) with glass substrate same "633"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 11:51
S42	2	refract\$4 near3 index same (SiC or silicon carbide) with glass substrate same "633"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 11:52
S43	9	refract\$4 near3 index same (SiC or silicon carbide) with glass substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 11:52
S44	50	silicon carbide with volume near3 ("45" or "50" or "55" or "60" or "65" or "70" or "75") and sputter \$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 13:37
S45	21	silicon carbide with target same volume	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 13:38
S46	46	silicon carbide with volume near3 ("45" or "50" or "55" or "60" or "65" or "70" or "75") and sputter \$3 not S45	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 13:38
S47	2	"5589116".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 14:46

S48	54	silicon carbide target with sputter \$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 16:01
S49	87	silicon carbide target	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 16:07
S50	33	silicon carbide target not S48	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 16:07
S51	1	weight near3 ration with impurit \$3 with silicon	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 16:13
S52	130	weight near3 ratio with impurit\$3 with silicon	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 16:13
S53	13	weight near3 ratio with impurit\$3 with silicon with "0.01"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 16:14
S54	4	silicon near5 (weight near3 ratio) with impurit \$3 with "0.01"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 16:17
S55	0	silicon near3 target near5 (weight near3 ratio) with impurit \$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 16:17

S56	41	silicon near5 (weight near3 ratio) with impurit \$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 16:17
S57	492	silicon carbide with volume and sputter\$3 not S45	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 17:43
S58	213	silicon carbide near5 volume and sputter\$3 not S45	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 17:44
S59	49	silicon carbide near5 volume near5 (ratio or percent) and sputter\$3 not S45	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 17:44
S60	50	silicon carbide near5 volume near5 (ratio or percent\$4) and sputter\$3 not S45	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/03 17:45
S61	4	"6733736"	US-PGPUB; USPAT	ADJ	ON	2008/06/04 13:28
S62	0	"7029643.pn"	US-PGPUB; USPAT	ADJ	ON	2008/06/04 13:29
S63	0	"7029643.pn"	US-PGPUB; USPAT	ADJ	ON	2008/06/04 13:29
S64	0	"7029643.pn."	US-PGPUB; USPAT	ADJ	ON	2008/06/04 13:29
S65	1	"7029643".pn.	US-PGPUB; USPAT	ADJ	ON	2008/06/04 13:29
S66	3	"6632761"	US-PGPUB; USPAT	ADJ	ON	2008/06/04 13:31
S67	1	"6387834".pn.	US-PGPUB; USPAT	ADJ	ON	2008/06/04 13:36
S68	90	bridgestone.as. and silicon carbide	US-PGPUB; USPAT	ADJ	ON	2008/06/04 13:37

S69	1	(09/941676).APP.	USPAT; USOCR	ADJ	ON	2008/06/04 13:40
S70	3	"7335330".pn. or "6632761".pn. or "6699411".pn.	USPAT; USOCR	ADJ	ON	2008/06/04 13:48
S71	839	204/298.13.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/24 16:38
S72	4	204/298.13.ccls. and silicon carbide with powder	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/24 16:38
S73	5	204/298.13.ccls. and silicon carbide with particle	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/24 16:38
S74	7	204/298.13.ccls. and silicon carbide same particle	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/24 16:39
S75	1	204/298.13.ccls. and silicon carbide same powder same size	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/24 16:39
S76	5	204/298.13.ccls. and silicon carbide same particle same size	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/24 16:39
S77	9399	silicon carbide same particle same size	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/24 16:41

S78	630	silicon carbide same particle same size and sputter\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/24 16:41
S79	32	silicon carbide same particle same size same target and sputter \$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/24 16:41
S80	2043	particle same size same target and sputter\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/24 16:50
S81	127	particle same size same target and sputter\$3 and 204/298.13.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/24 16:50
S82	0	silicon carbide same volume ratio same particle size same ("2.3") same ("16.4")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/25 08:35
S83	0	volume near3 ratio same particle same size same ("2.3") same ("16.4") and sputter\$3 and target	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/25 08:35
S84	0	volume near3 ratio same particle same size same ("2.3") same ("16.4")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/25 08:35
S85	342	particle same size same target same (micron or micrometer) and sputter\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/25 08:59

S86	127	particle same size same target and sputter\$3 and 204/298.13.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/25 08:59
S87	315	particle same size same target same (micron or micrometer) and sputter\$3 not S86	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/25 08:59
S88	2490	volume near3 ratio and sputter\$3 and target	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/25 10:13
S89	14	(silicon carbide or SiC) same volume near3 ratio and sputter\$3 and target	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/25 10:13
S90	7	(silicon carbide or SiC) same weight near3 ratio and sputter\$3 and target	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/25 10:16
S91	47	(silicon carbide or SiC) same atomic near3 ratio and sputter\$3 and target	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/25 10:17
S92	613	(silicon carbide or SiC) same ratio and sputter\$3 and target	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/25 10:23
S93	280	(silicon carbide or SiC) with ratio and sputter\$3 and target	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/25 10:23

S94	8	"4917970".pn. or "4525461".pn. or "5182059".pn. or "4925815".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/25 10:27
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